/ Descriptions

WR0<5 ṂṂ Ḅ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

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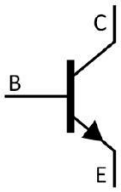
High gain, good linearity of h_{FE}.

/ Applications

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TV final picture IF amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Collector PIN 2 χ Emitter PIN 3 χ Base

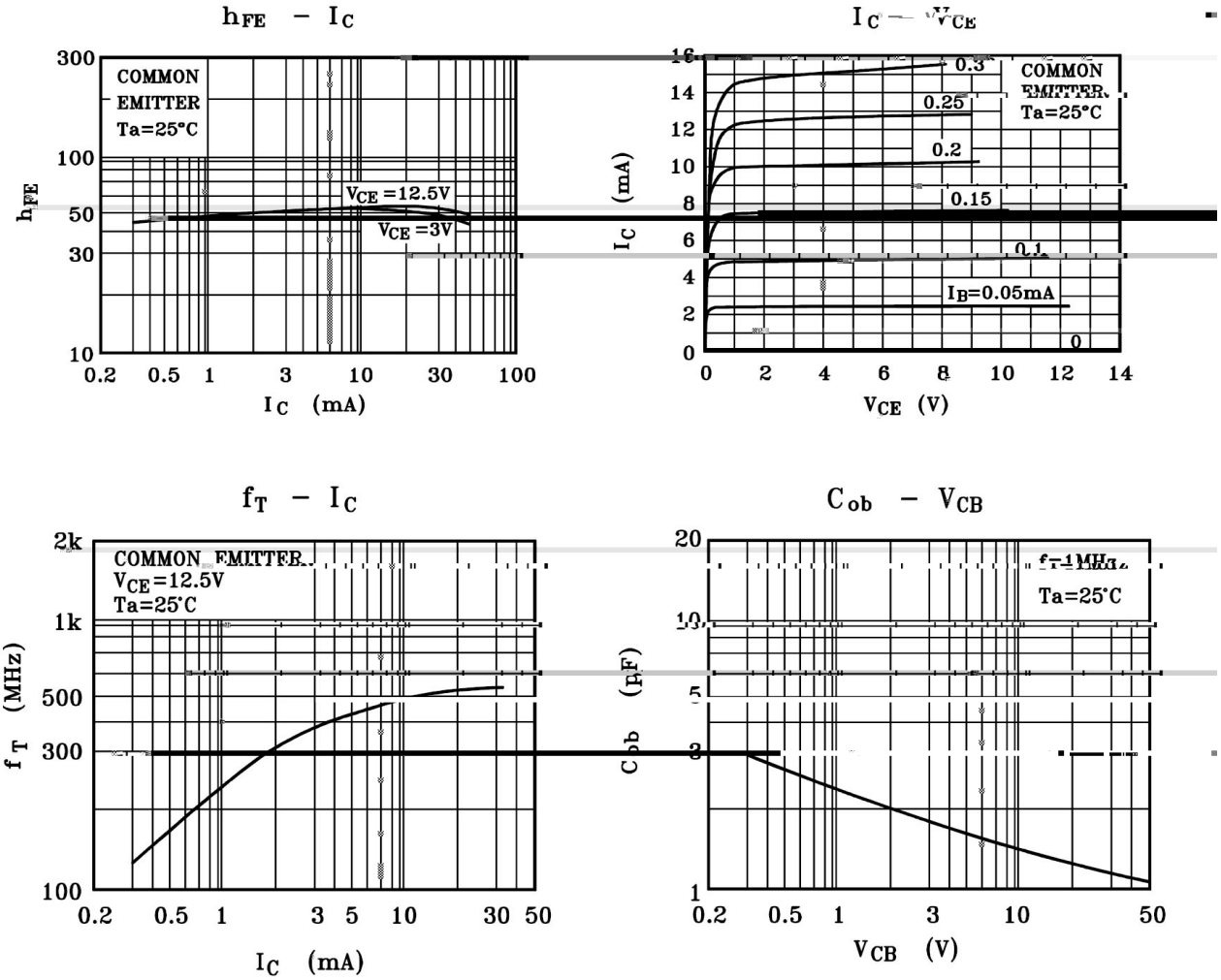
/ hFE Classifications & Marking

ð м ㄱ ب ˝ See Marking Instructions.

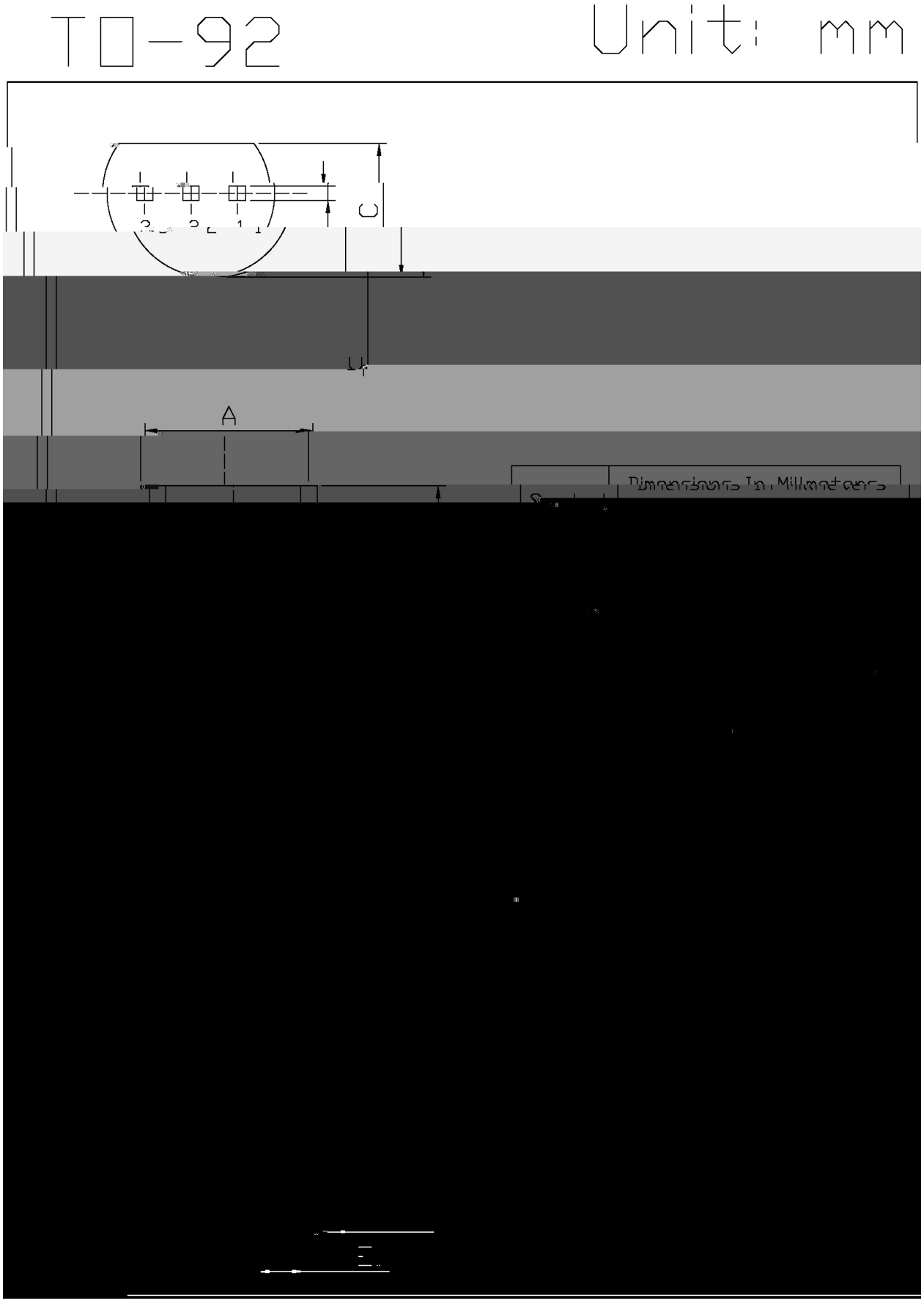
v ˝Ọ Parameter	٢ N Symbol	˝Ọ Ö Rating	D Ꮋ Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ˝Ọ Parameter	٢ N Symbol	ᗻ ; ˆ ٢ Test Conditions	ѡ ṇ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ꮋ Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	25			V

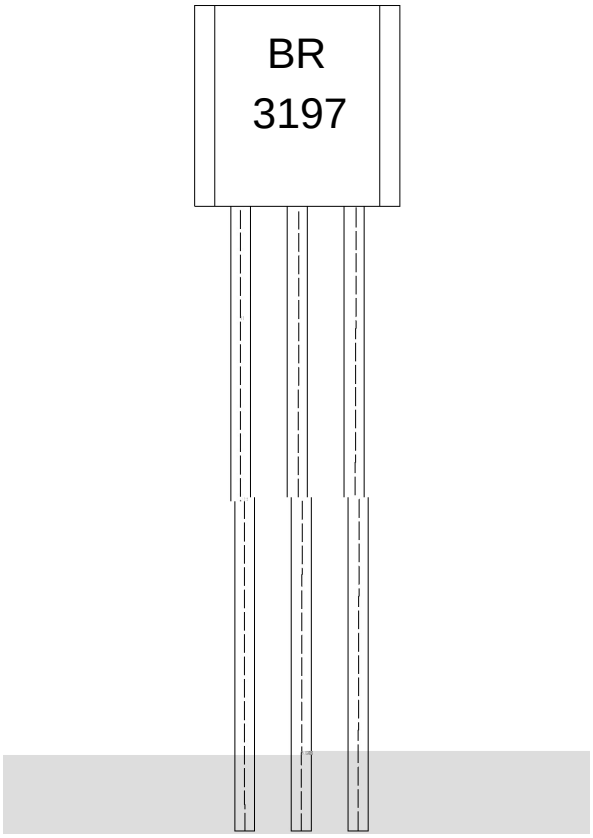
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



ب ˝ χ

EU= ѭ ҙ И Ґђ

64<: χ ѭ ҙ N Ґђ

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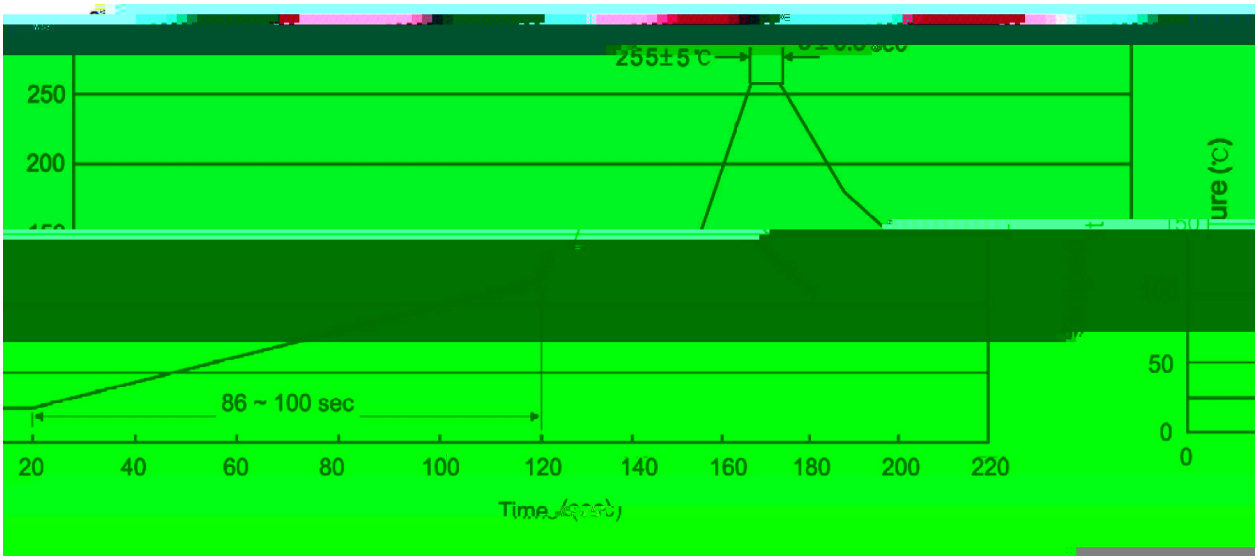
Note:

BR: Company Code.

3197: Product Type.

****: Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł	ˋH ڑ χ 10 ° 1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

ˈQ ţ ﾔ Ł / BULK